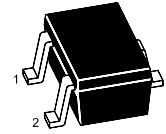


MMBT8550W

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications



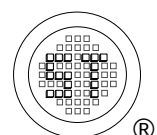
1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

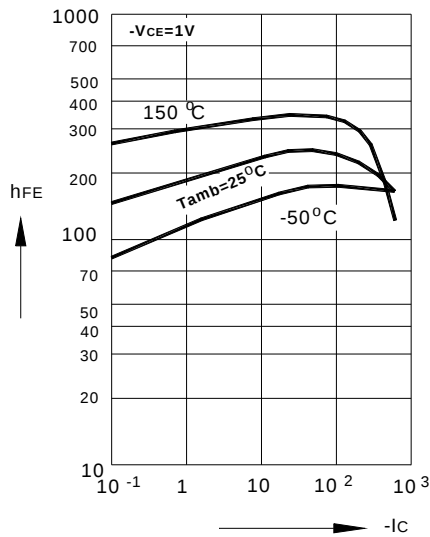
Parameter	Symbol	Value	Unit
Collector Emitter Voltage	$-V_{CEO}$	25	V
Collector Base Voltage	$-V_{CBO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	600	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

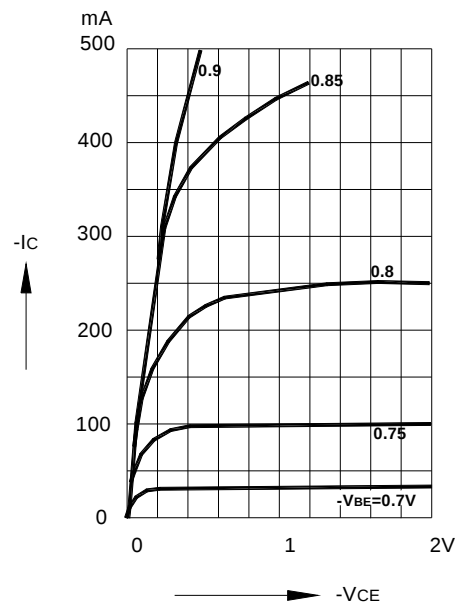
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$	h_{FE}	100	-	250	-
MMBT8550CW	h_{FE}	160	-	400	-
MMBT8550DW	h_{FE}	40	-	-	-
at $-V_{CE} = 1\text{ V}$, $-I_C = 500\text{ mA}$					
Collector Cutoff Current at $-V_{CB} = 35\text{ V}$	$-I_{CBO}$	-	-	100	nA
Collector Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_E = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V
Base Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_E = 50\text{ mA}$	$-V_{BE(sat)}$	-	-	1.2	V
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	25	-	-	V
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V
Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 50\text{ MHz}$	f_T	-	100	-	MHz
Collector Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{CBO}	-	12	-	pF



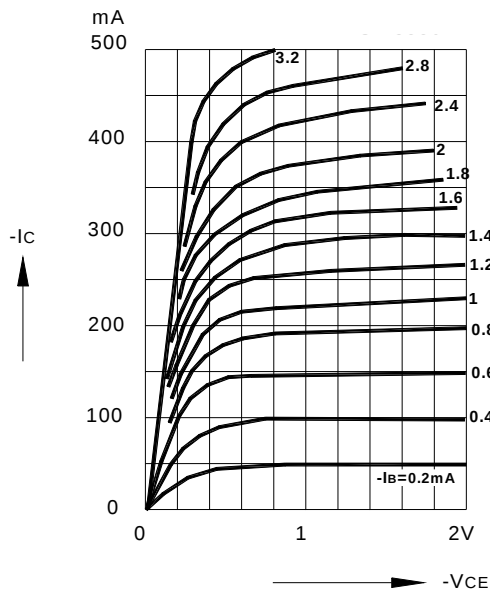
DC current gain
versus collector current



Common emitter
collector characteristics



Common emitter
collector characteristics



Common emitter
collector characteristics

